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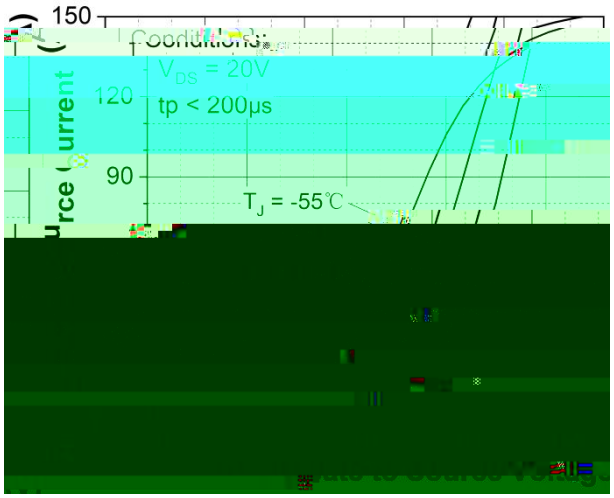
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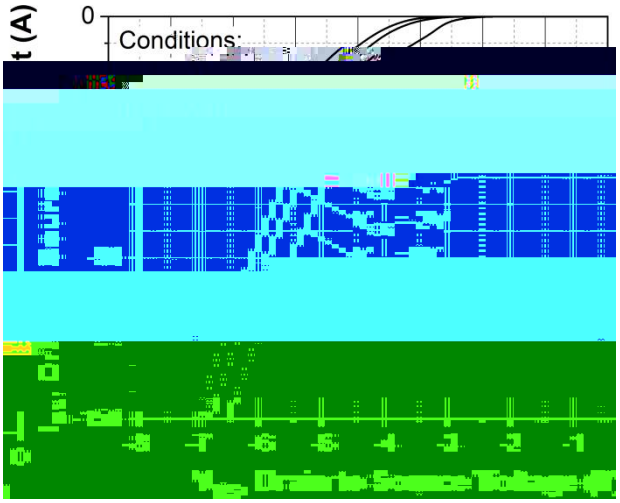
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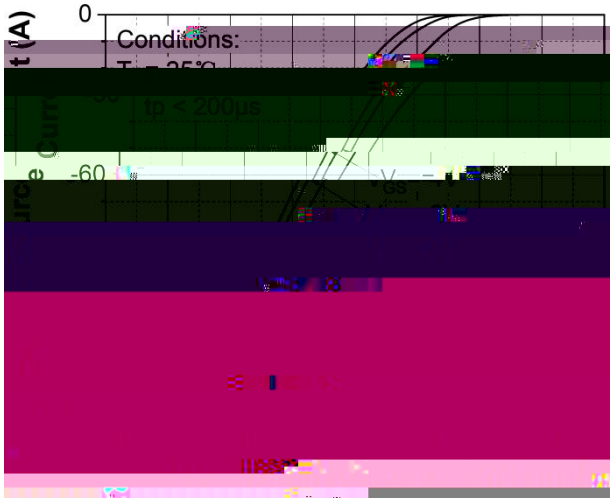
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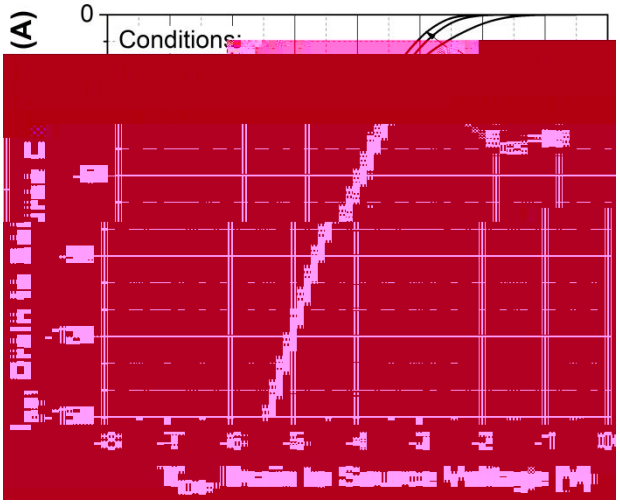


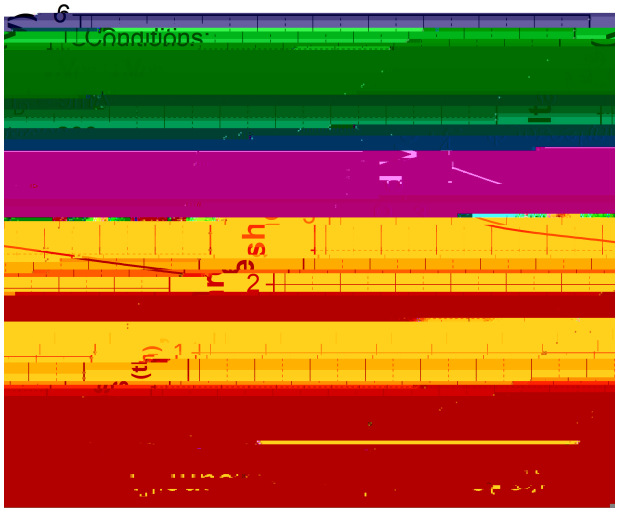
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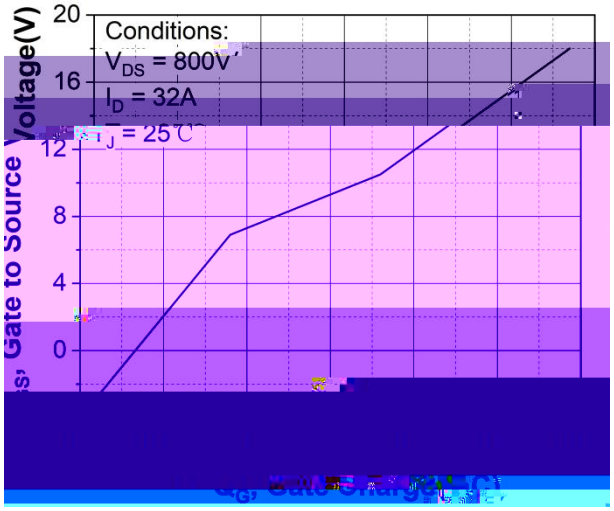

150
120
90
Conditions:
$V_{DS}$ = 20V
tp < 200μs
$T_J$ = -55℃

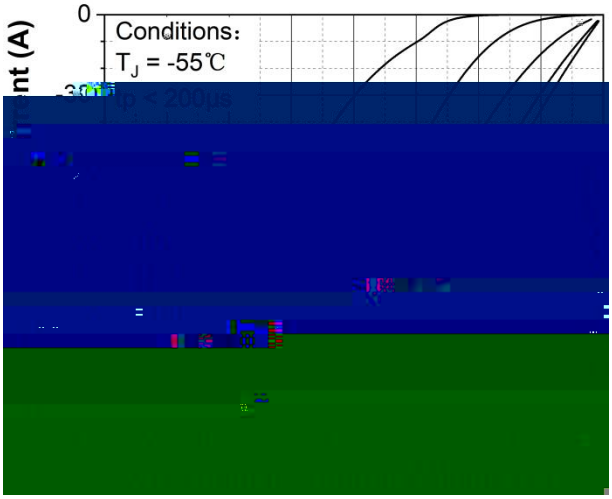

0
Conditions:

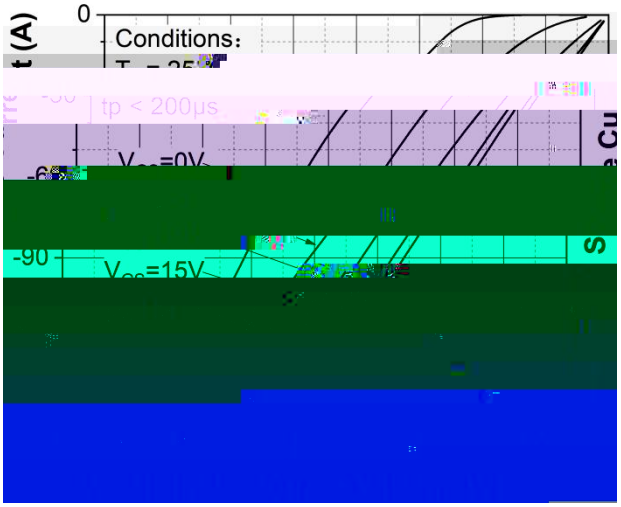

0
Conditions:
tp < 200μs
-60

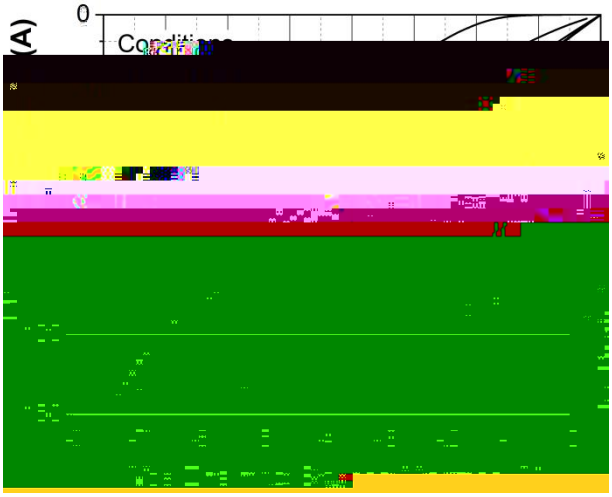

0
Conditions:

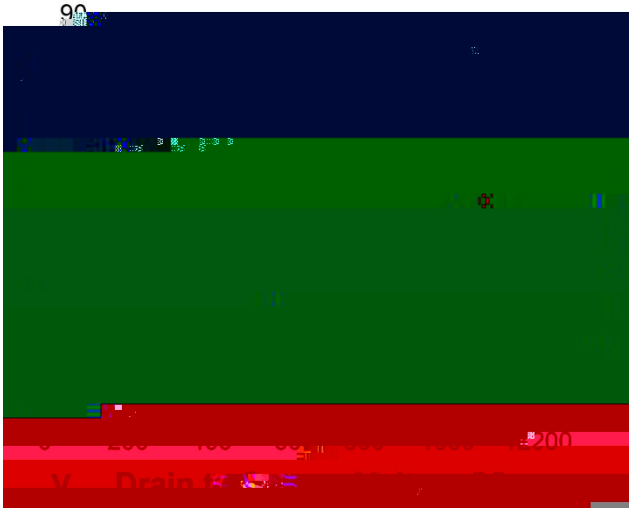

Conditions:
2
1

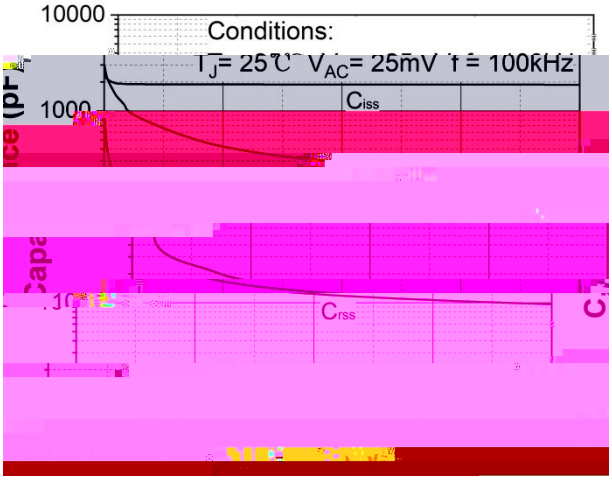

20
16
12
8
4
0
Conditions:
$V_{DS}$ = 800V
$I_D$ = 32A
$T_J$ = 25℃

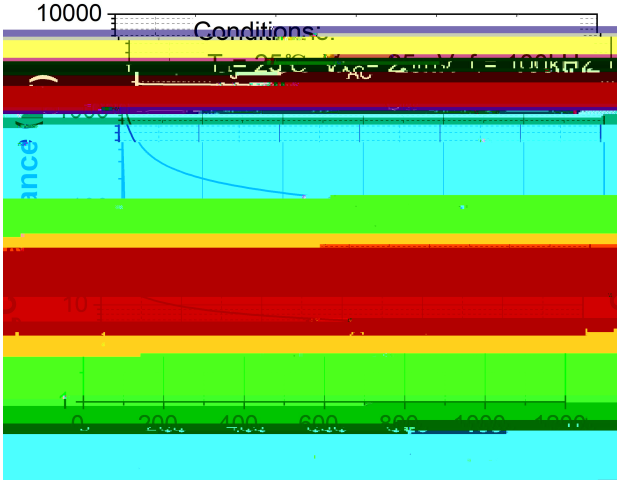

0
Conditions:
$T_J$ = -55℃
tp < 200μs

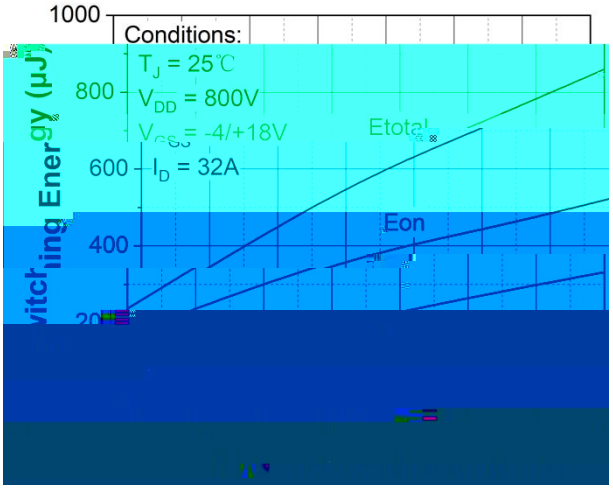

0
Conditions:
tp < 200μs
-90

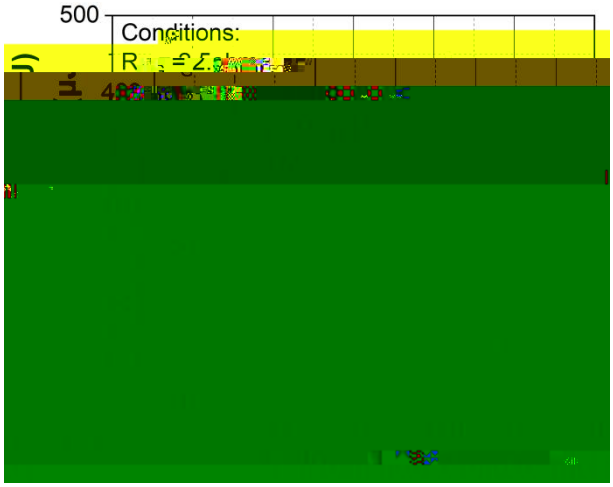

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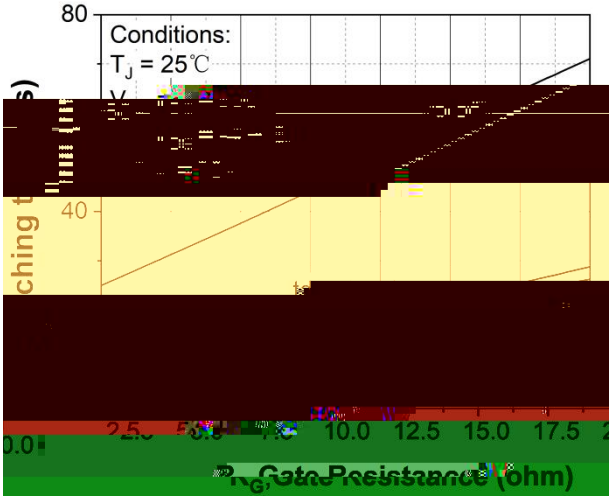

90

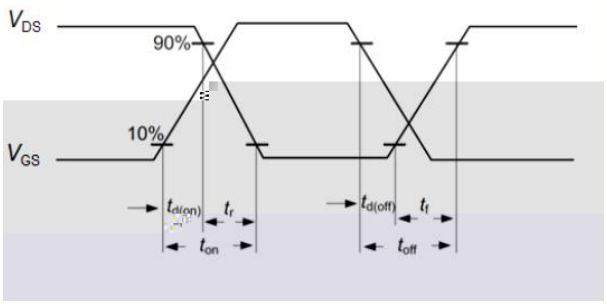

10000
Conditions:
$T_J$= 25℃ $V_{AC}$= 25mV f = 100kHz
1000
$C_{iss}$
$C_{rss}$

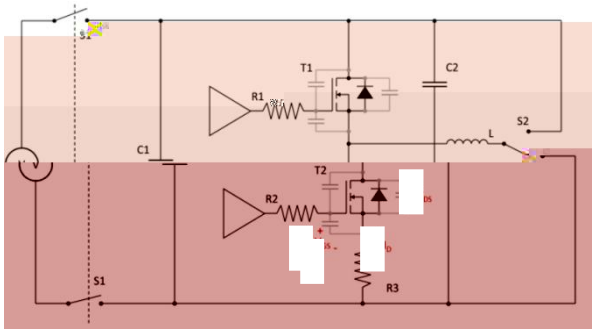

10000
Conditions:
1000
10
1

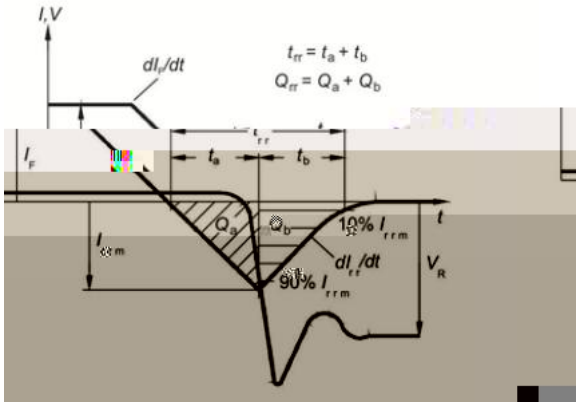

1000
Conditions:
$T_J$ = 25℃
$V_{DD}$ = 800V
$V_{GS}$ = -4/+18V
$I_D$ = 32A
800
600
400
Etotal
Eon
Energy (μJ)


500
Conditions:


80
Conditions:
$T_J$ = 25℃
40
10.0
12.5
15.0
17.5
Gate Resistance (ohm)


$V_{DS}$
90%
10%
$V_{GS}$
$t_{d(on)}$
$t_r$
$t_{on}$
$t_{d(off)}$
$t_f$
$t_{off}$


S2
T1
C2
R1
S2
L
C1
T2
R2
R3
S1


I,V
$dI_F/dt$
$t_{rr} = t_a + t_b$
$Q_{rr} = Q_a + Q_b$
$I_F$
$t_a$
$t_b$
$Q_a$
$Q_b$
10% $I_{rrm}$
t
$I_{rrm}$
$dI_{rr}/dt$
90% $I_{rrm}$
$V_R$

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